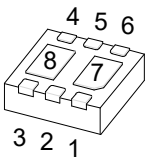
USS4260PAN

DUAL TRANSISTOR

COMPLEMENTARY NPN/NPN LOW $V_{CE(SAT)}$ (BISS) TRANSISTOR



DFN2020-6C

■ DESCRIPTION

The UTC **USS4260PAN** is an NPN low $V_{CE(SAT)}$ Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6C Surface-Mounted Device (SMD) plastic package.

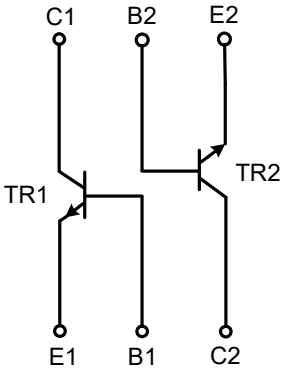
NPN complement: USS4260PANP

PNP complement: USS5260PAP

■ FEATURES

* Very low collector-emitter saturation voltage $V_{CE(SAT)}$
* High collector current capability I_C and I_{CM}
* High collector current gain h_{FE} at high I_C
* Reduced Printed-Circuit Board (PCB) requirements
* High efficiency due to less heat generation
* Green & Pb Free

■ EQUIVALENT CIRCUIT



■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment								Packing
		1	2	3	4	5	6	7	8	
USS4260PANG-K06C-2020-R	DFN2020-6C	E1	B1	C2	E2	B2	C1	C1	C2	Tape Reel

Note: Pin Assignment: E: Emitter B: Base C: Collector

USS4260PANG-K06C-2020-R

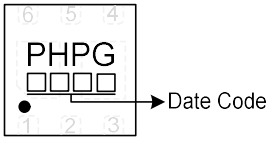
(1)Packing Type — (1) R: Tape Reel

(2)Package Type — (2) K06C-2020: DFN2020-6C

(3)Green Package — (3) G: Halogen Free and Lead Free

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■ MARKING



■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	2	A
Peak Collector Current	I_{CM}	3	A
Collector Current	I_B	0.3	A
Peak Collector Current	I_{BM}	1	A
Collector Power Dissipation	P_C	370	mW
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

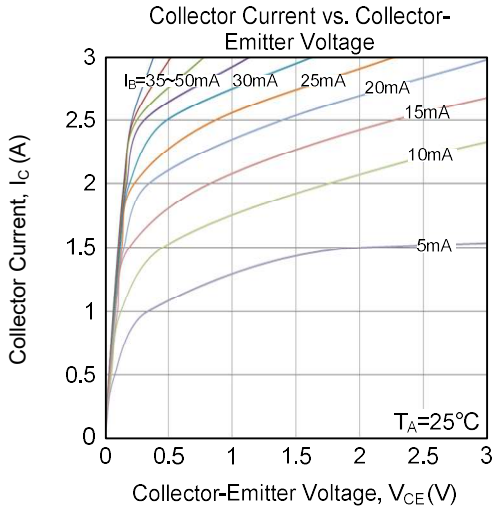
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	338	°C/W

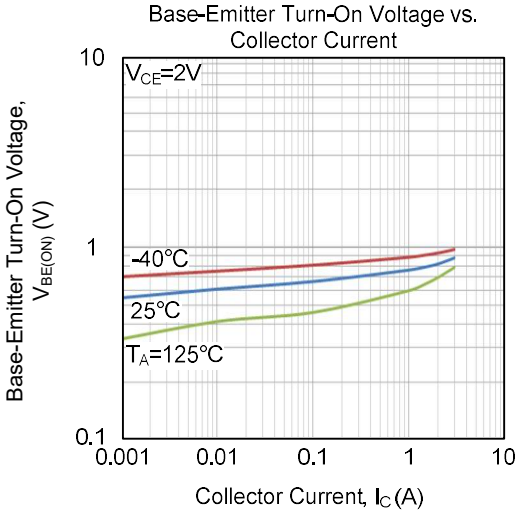
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

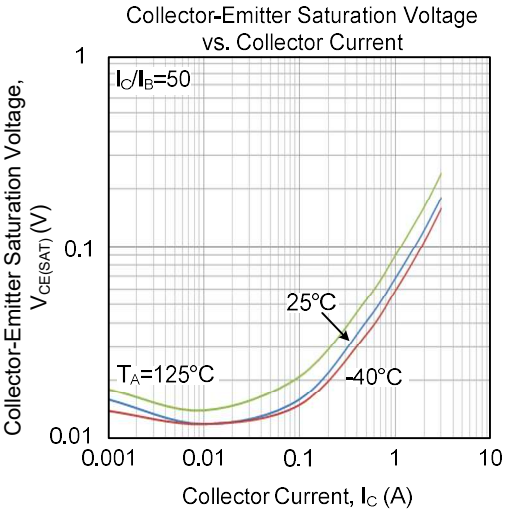
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

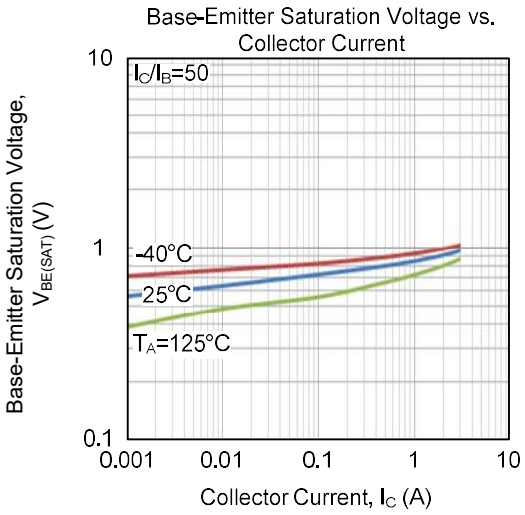
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
PER TRANSISTOR						
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=100μA, I_E=0	60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA, I_B=0	60			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=100μA, I_C=0	7			V
Collector-Base Cut-off Current	I_{CBO}	V_{CB}=48V, I_E=0			100	nA
Emitter-Base Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0			100	nA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=500mA, I_B=50mA			90	mV
		I_C=1A, I_B=50mA			180	mV
		I_C=2A, I_B=100mA			350	mV
		I_C=2A, I_B=200mA			330	mV
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C=500mA, I_B=50mA			1	V
		I_C=1A, I_B=50mA			1	V
		I_C=2A, I_B=100mA			1.1	V
		I_C=2A, I_B=200mA			1.2	V
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	V_{CE}=2V, I_C=0.5A			0.9	V
DC Current Gain	h_{FE}	V_{CE}=2V, I_C=100mA	290			
		V_{CE}=2V, I_C=500mA	210			
		V_{CE}=2V, I_C=1A	120			
		V_{CE}=2V, I_C=2A	50			
Collector Capacitance	C_{OB}	V_{CB}=10V, I_E=i_e=0A, f=1MHz		14	17	pF

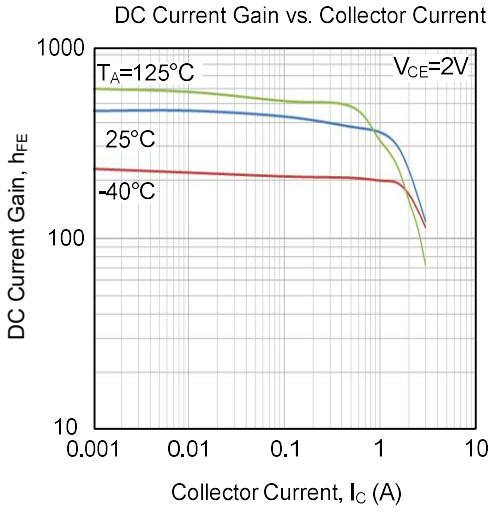
■ TYPICAL CHARACTERISTICS

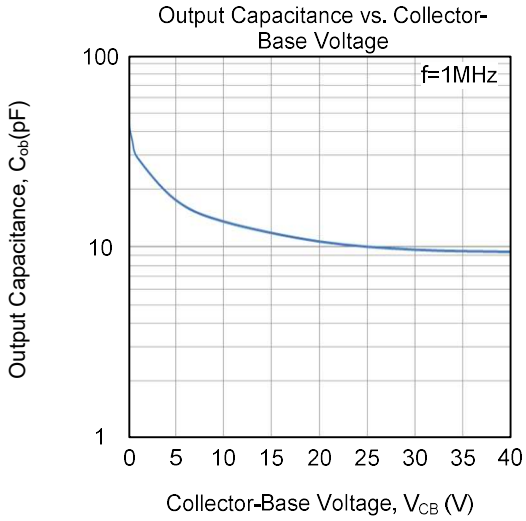




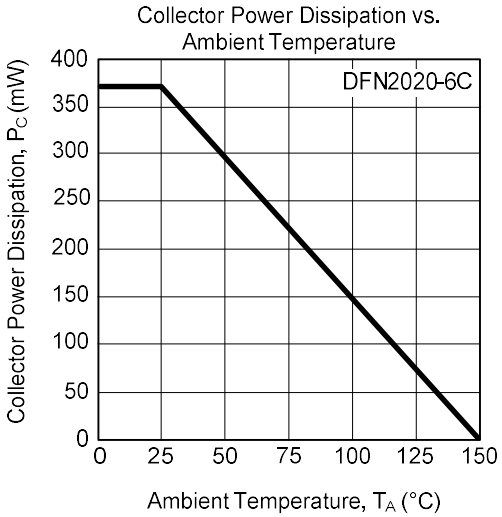








■ TYPICAL CHARACTERISTICS (Cont.)



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